ABSTRACT

Disclosed is a blankmask for EUV lithography, including a reflective film, a capping film and a phase shift film which are sequentially formed on a substrate. The phase shift film includes a first layer containing niobium (Nb) and chrome (Cr), and a second layer containing tantalum (Ta) and silicon (Si). In the first layer, the content of niobium (Nb) ranges from 20 to 50 at%, and the content of chrome (Cr) content ranges from 10 to 40 at%. The blankmask can implement an excellent resolution and NILS, and implement a low DtC.

FIG. 3